

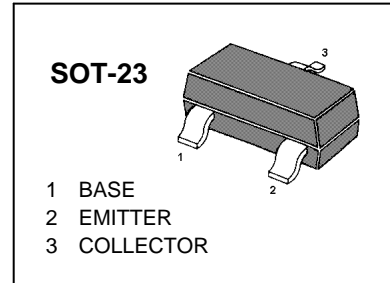
S9014

TRANSISTOR (NPN)

FEATURES

Complementary to S9015

MARKING: J6



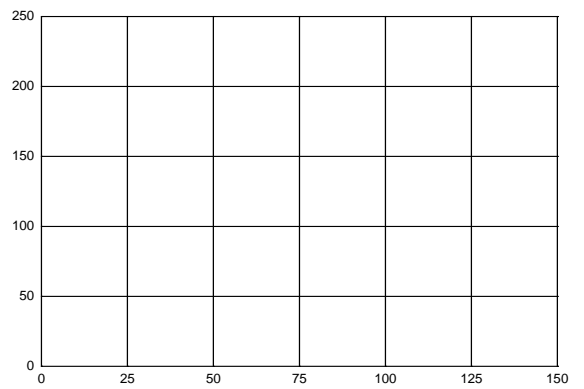
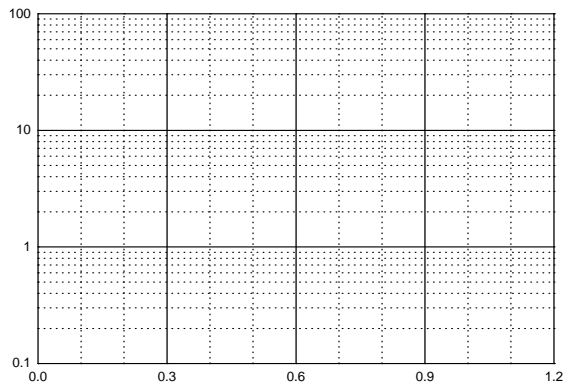
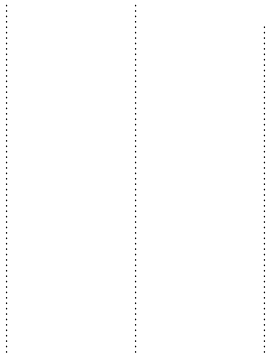
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	value	units
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	0.1	A
P_C	Collector Power Dissipation	0.2	W
T_J	Junction Temperature	150	
T_{STG}	Storage Temperature	-55-150	

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}$, $I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}$, $I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=35\text{V}$, $I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3\text{V}$, $I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}$, $I_C=1\text{mA}$	200		450	
Collector-emitter saturation voltage	$V_{CE(Sat)}$	$I_C=100\text{mA}$, $I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(Sat)}$	$I_C=100\text{mA}$, $I_B=5\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=5\text{V}$, $I_C=10\text{mA}$ $f=30\text{MHz}$	150			MHz

Typical Characteristics





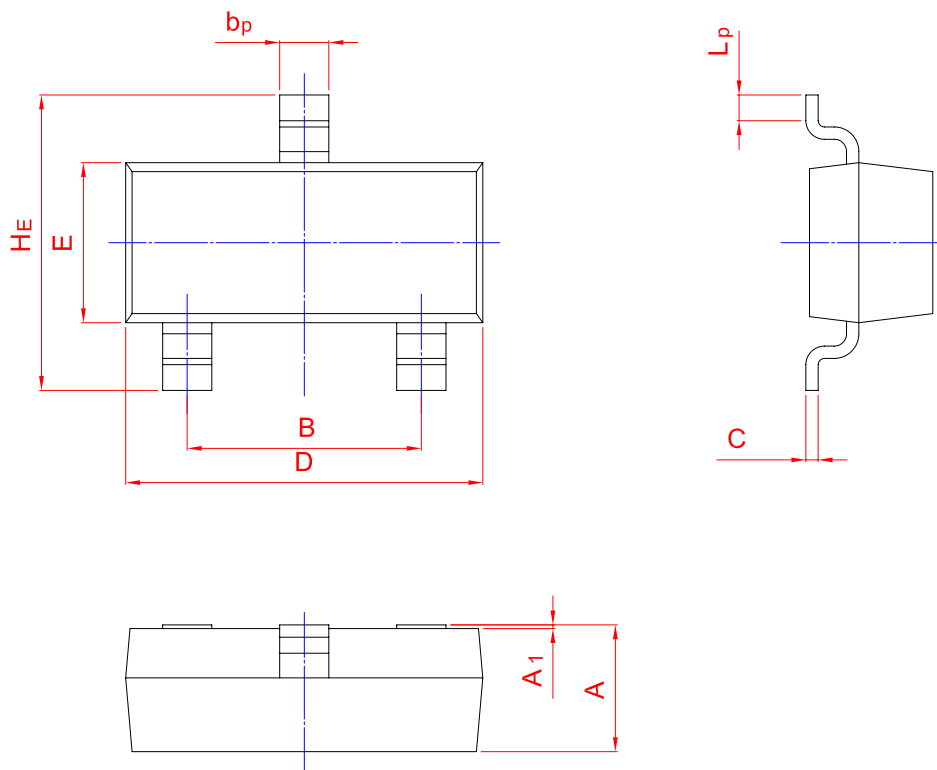
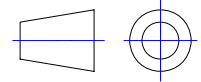
S9014

TRANSISTOR (NPN)

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20